

Title (en)

METHOD FOR PRODUCING A DIELECTRIC MAGNETO RESISTOR IN A SUBSTRATE TRENCH, A CORRESPONDING SUBSTRATE, AND A POWER TRANSISTOR

Title (de)

VERFAHREN ZUR HERSTELLUNG EINER DIELEKTRISCHEN FELDPLATTE IN EINEM GRABEN EINES SUBSTRATS, ENTSPRECHENDE SUBSTRAT UND LEISTUNGSTRANSISTOR

Title (fr)

PROCÉDÉ DE FORMATION D'UNE PLAQUE DE CHAMP DIÉLECTRIQUE DANS UNE TRANCHÉE D'UN SUBSTRAT, SUBSTRAT CORRESPONDANT ET TRANSISTOR DE PUISSANCE

Publication

EP 3127161 A1 20170208 (DE)

Application

EP 15708232 A 20150309

Priority

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- EP 2015054821 W 20150309

Abstract (en)

[origin: WO2015150023A1] Substrates comprising a trench with walls and a base are increasingly used for standard components. The invention relates to a substrate characterised in that it comprises a dielectric magneto resistor (83) consisting of at least one first dielectric layer, which only adjoins the lower sections of the trench walls and the base of said trench (60). Parasitic capacitances can be reduced when using this substrate for power transistors.

IPC 8 full level

H01L 21/336 (2006.01); **H01L 29/423** (2006.01); **H01L 29/739** (2006.01); **H01L 29/78** (2006.01)

CPC (source: EP US)

H01L 29/1095 (2013.01 - EP US); **H01L 29/1608** (2013.01 - EP US); **H01L 29/407** (2013.01 - US); **H01L 29/41766** (2013.01 - EP US); **H01L 29/4236** (2013.01 - EP US); **H01L 29/42368** (2013.01 - EP US); **H01L 29/66068** (2013.01 - EP US); **H01L 29/66734** (2013.01 - US); **H01L 29/7813** (2013.01 - EP US)

Citation (search report)

See references of WO 2015150023A1

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